REMARKS

The specification has been amended to correct minor informalities. No new matter has been added.

Should the Examiner believe that anything further would be desirable to place this application in better condition for allowance, the Examiner is invited to contact Applicant's undersigned attorney at the telephone number listed below.

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION:

Please amend the specification as follows:

Please replace the paragraph bridging page 4 and 5 with the following:

According to the present invention disclosed in the present specification, chlorine is also contained in the atmosphere in order to promote the effect of gettering the [met] metal. The effect of eliminating the metal element from the silicon film may be enhanced by forming a compound of the metal element, fluorine and chlorine at the time of gettering by introducing chlorine.

On page 21, please replace the third paragraph with the following:

It is also effective to include fluorine within the atmosphere in forming the thermal oxide film 211. If fluorine is included in the atmosphere in forming the thermal oxide film 211, the nickel element may be fixed and unpaired [bonding hands] bonds on the surface of the silicon film may be neutralized. That is, the interfacial characteristics between the active layer and the gate insulating film may be improved.

On page 30, please replace the first paragraph with the following:

Then, contact holes are created to form a source electrode 416 and a drain electrode 417. Finally, a heat treatment of an hour is implemented within a hydrogen atmosphere at 350° C (hydrogen heat treatment). In this step, the defects and unpaired [coupling hands] bonds within the active layer are neutralized. Thus, the thin film transistor shown in FIG. 4E is completed.